

## HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

- SGS-THOMSON PREFERRED SALESTYPE
- NPN TRANSISTOR
- HIGH VOLTAGE CAPABILITY
- LOW SPREAD OF DYNAMIC PARAMETERS
- MINIMUM LOT-TO-LOT SPREAD FOR RELIABLE OPERATION
- VERY HIGH SWITCHING SPEED
- FULLY CHARACTERIZED AT 125°C
- LARGE RBSOA
- FULLY MOLDED ISOLATED PACKAGE
- 2000 V DC ISOLATION (U.L. COMPLIANT)

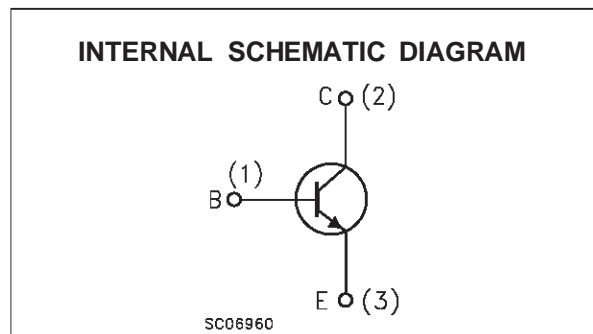
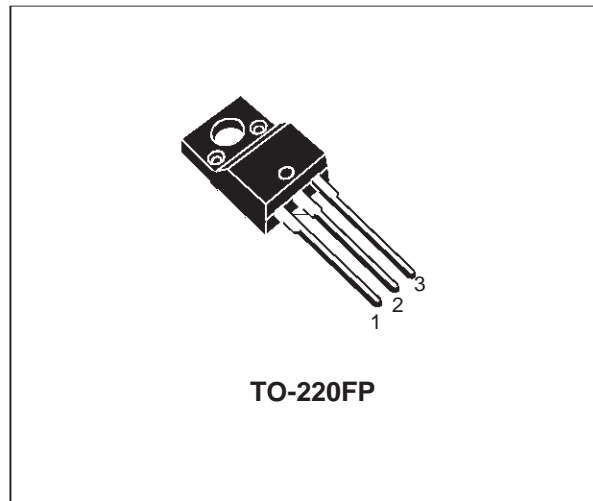
### APPLICATIONS

- ELECTRONIC BALLASTS FOR FLUORESCENT LIGHTING
- FLYBACK AND FORWARD SINGLE TRANSISTOR LOW POWER CONVERTERS

### DESCRIPTION

The BUL310FP is manufactured using high voltage Multi Epitaxial Planar technology for high switching speeds and high voltage capability. It uses a Cellular Emitter structure with planar edge termination to enhance switching speeds while maintaining a wide RBSOA.

The BUL series is designed for use in lighting applications and low cost switch-mode power supplies.



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_{CES}$	Collector-Emitter Voltage ( $V_{BE} = 0$ )	1000	V
$V_{CEO}$	Collector-Emitter Voltage ( $I_B = 0$ )	500	V
$V_{EBO}$	Emitter-Base Voltage ( $I_C = 0$ )	9	V
$I_C$	Collector Current	5	A
$I_{CM}$	Collector Peak Current ( $t_p < 5$ ms)	10	A
$I_B$	Base Current	3	A
$I_{BM}$	Base Peak Current ( $t_p < 5$ ms)	4	A
$P_{tot}$	Total Dissipation at $T_c = 25$ °C	36	W
$T_{stg}$	Storage Temperature	-65 to 150	°C
$T_j$	Max. Operating Junction Temperature	150	°C

# BUL310FP

## THERMAL DATA

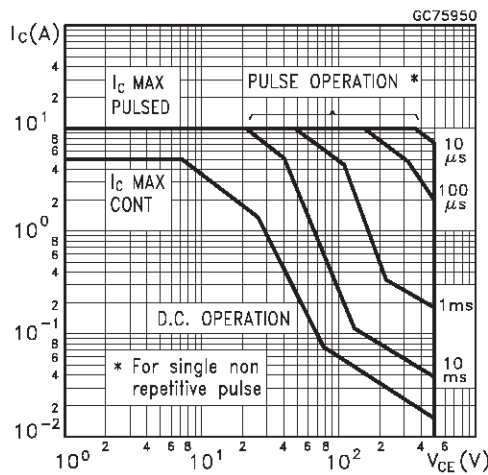
R <sub>thj-case</sub>	Thermal Resistance Junction-Case	Max	3.5	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-Ambient	Max	62.5	°C/W

## ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

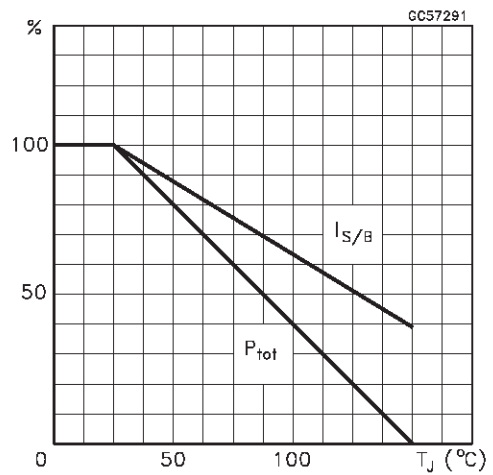
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I <sub>CES</sub>	Collector Cut-off Current (V <sub>BE</sub> = 0)	V <sub>CE</sub> = 1000 V V <sub>CE</sub> = 1000 V T <sub>j</sub> = 125 °C			100 500	μA μA
I <sub>CEO</sub>	Collector Cut-off Current (I <sub>B</sub> = 0)	V <sub>EC</sub> = 400 V			250	μA
V <sub>CEO(sus)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 100 mA L = 25 mH	500			V
V <sub>EBO</sub>	Emitter-Base Voltage (I <sub>C</sub> = 0)	I <sub>E</sub> = 10 mA	9			V
V <sub>CE(sat)*</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1 A I <sub>B</sub> = 0.2 A I <sub>C</sub> = 2 A I <sub>B</sub> = 0.4 A I <sub>C</sub> = 3 A I <sub>B</sub> = 0.6 A			0.5 0.7 1.1	V V V
V <sub>BE(sat)*</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 1 A I <sub>B</sub> = 0.2 A I <sub>C</sub> = 2 A I <sub>B</sub> = 0.4 A I <sub>C</sub> = 3 A I <sub>B</sub> = 0.6 A			1 1.1 1.2	V V V
h <sub>FE*</sub>	DC Current Gain	I <sub>C</sub> = 10 mA V <sub>CE</sub> = 5 V I <sub>C</sub> = 3 A V <sub>CE</sub> = 2.5 V	10	10		
t <sub>s</sub> t <sub>f</sub>	INDUCTIVE LOAD Storage Time Fall Time	I <sub>C</sub> = 2 A I <sub>B1</sub> = 0.4 A V <sub>BE(off)</sub> = -5 V R <sub>BB</sub> = 0 Ω V <sub>CL</sub> = 250 V L = 200 μH		1.2 80	1.9 160	μs ns
t <sub>s</sub> t <sub>f</sub>	INDUCTIVE LOAD Storage Time Fall Time	I <sub>C</sub> = 2 A I <sub>B1</sub> = 0.4 A V <sub>BE(off)</sub> = -5 V R <sub>BB</sub> = 0 Ω V <sub>CL</sub> = 250 V L = 200 μH T <sub>j</sub> = 125 °C		1.8 150		μs ns

\* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

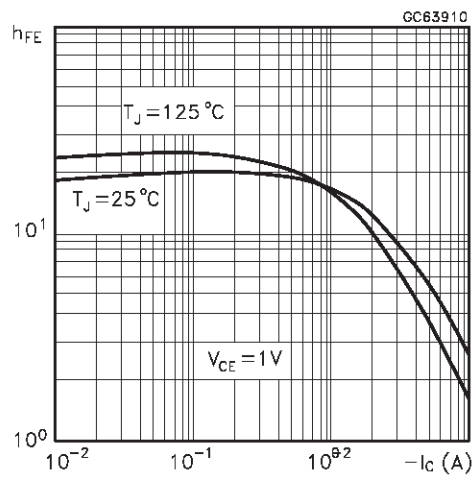
## Safe Operating Areas



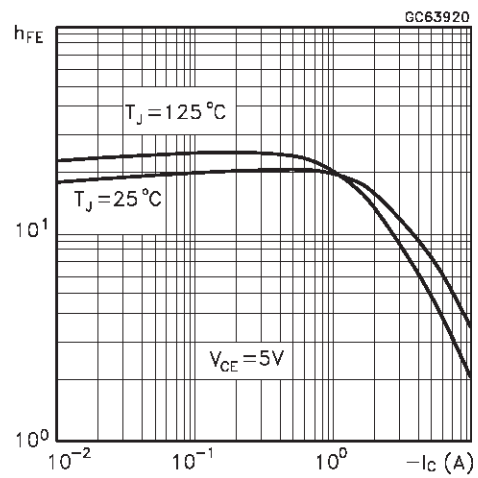
## Derating Curve



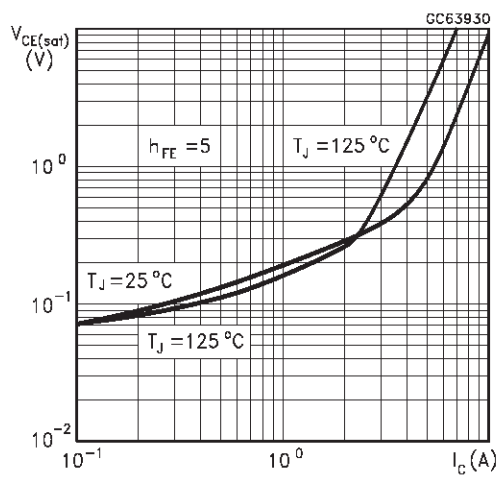
DC Current Gain



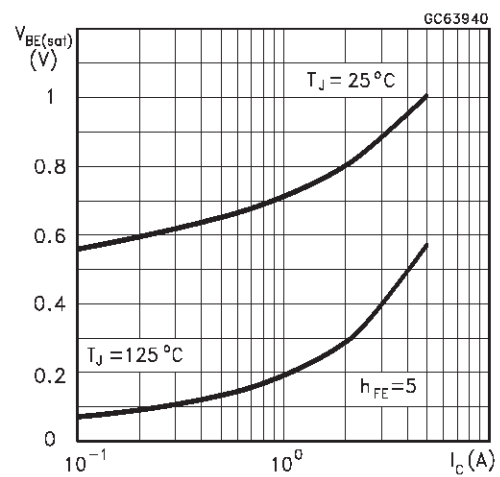
DC Current Gain



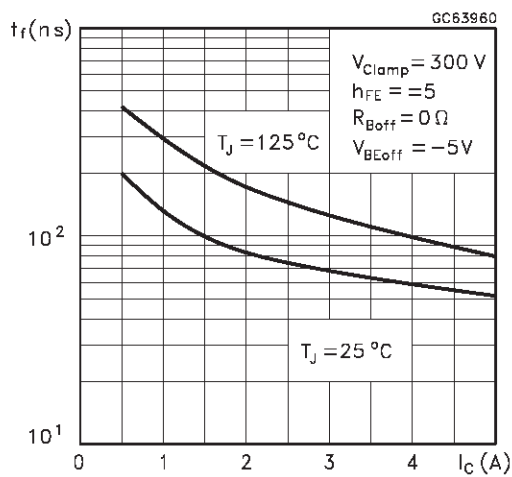
Collector Emitter Saturation Voltage



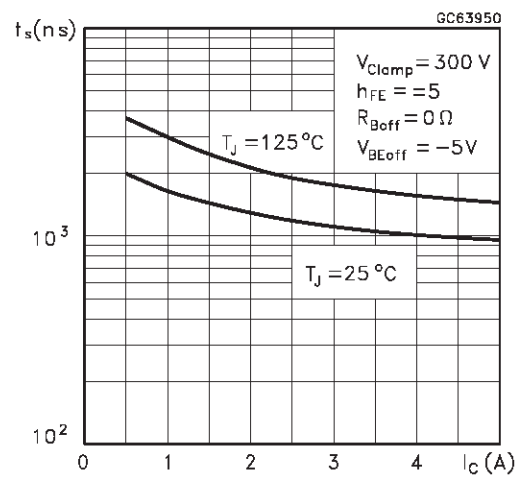
Base Emitter Saturation Voltage



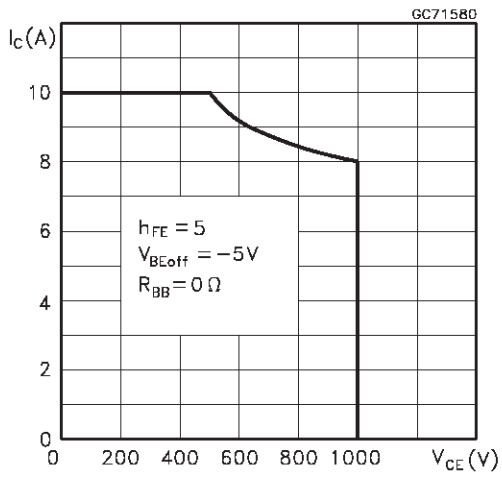
Inductive Fall Time



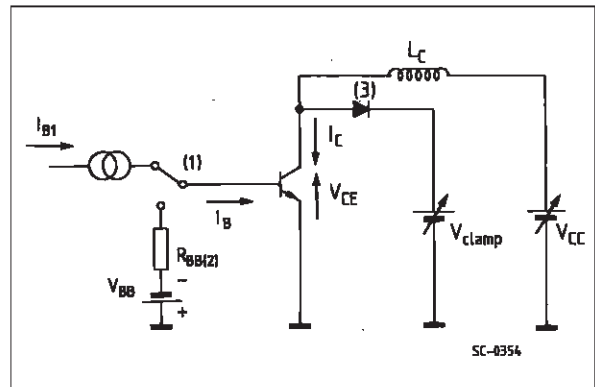
Inductive Storage Time



Reverse Biased SOA



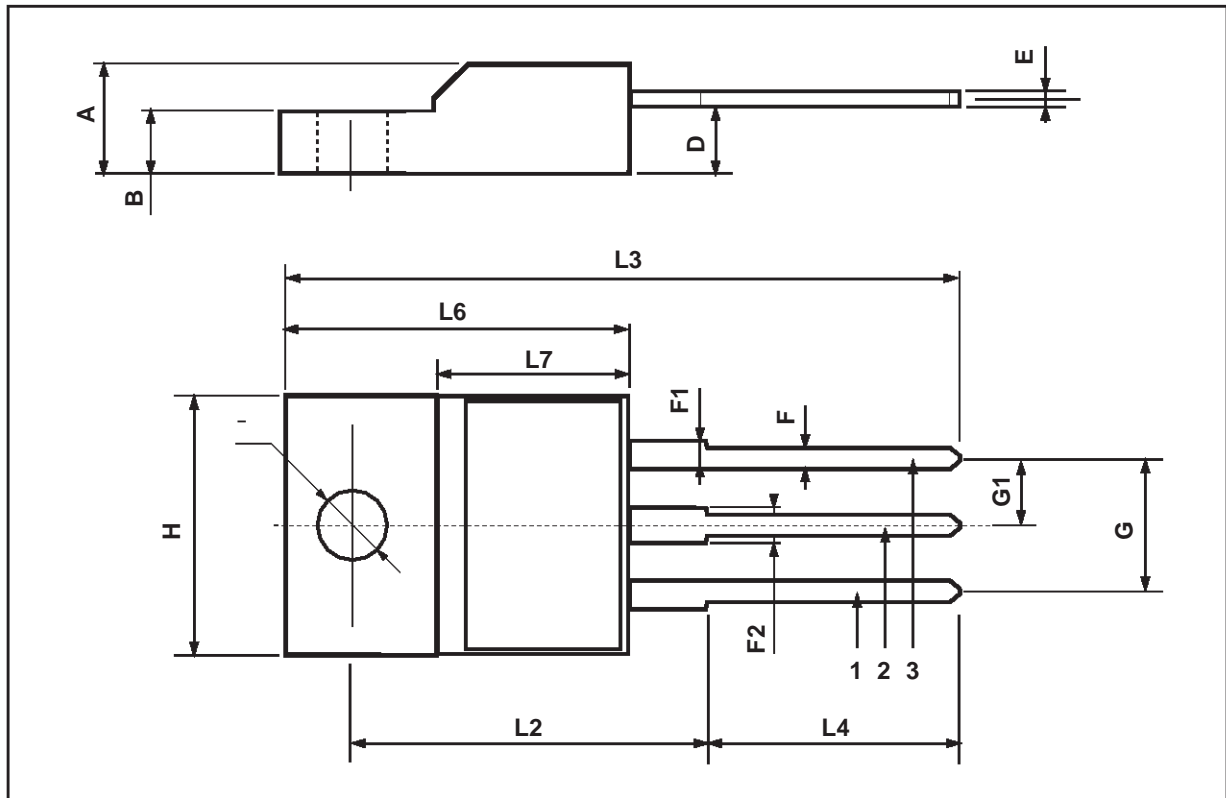
RBSOA and Inductive Load Switching Test Circuit



- (1) Fast electronic switch
- (2) Non-inductive Resistor
- (3) Fast recovery rectifier

TO-220FP MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



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